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Abstract

Method for minimizing the vapor deposition of tungsten oxide during the selective side wall oxidation of tungsten-silicon gates

During the selective oxidation of gate structures which include a polycrystalline silicon layer and a tungsten layer, which is known per se, the vapor deposition of tungsten oxide is prevented or at least greatly reduced by a special process. The gate structure is acted on by a hydrogen-containing, nonaqueous inert gas before and, if appropriate, after a treatment step with a hydrogen/water mixture.

(Fig. 3 to be published with the abstract)